

Dear Editor and Reviewers,

We sincerely thank you for taking the time to review our manuscript “Iron’s impact on silicon solar cell execution: comprehensive modeling across diverse scenarios” (Ms. Ref. No.: MSB-S-24-02710). Your insightful comments and constructive suggestions have greatly helped us improve the quality of our work. We particularly appreciate your careful reading and thoughtful feedback, which have led to significant improvements in both the technical content and presentation clarity of our manuscript. We have carefully addressed all the comments and made corresponding revisions to the manuscript. Below we provide our detailed point-by-point responses to each comment. We hope the revised manuscript better meets your expectations and standards for publication in Materials Science and Engineering: B.

Response to Reviewer #1

Comment 1. *The author must explain the specific mechanisms you propose for the interaction between iron-related defects and other impurities in silicon solar cells? How might these interactions complicate the interpretation of photovoltaic performance metrics?*

Reply:

In general, interstitial iron is already mobile at room temperature and can interact with various impurities. Over 30 iron-related complexes have been identified in silicon, and nearly 25 energy levels associated with iron-related defects have been reported in the silicon bandgap across different studies [1, 2, 3]. For example, iron forms complexes with carbon, oxygen, hydrogen, sulfur, and other metal impurities, as well as with native defects in silicon. However, in terms of their impact on photovoltaic performance, two primary factors must be considered. First, the concentration of the relevant defects is crucial. It is widely recognized that in *p*-type silicon under equilibrium conditions, most iron impurity atoms pair with acceptors (e.g., boron in Si:B) [4, 1]. The concentration of other complexes is significantly lower, and detailed investigation of these complexes requires specialized sample preparation, such as additional doping with other expected complex components or irradiation to increase the concentration of native defects [5]. Further supporting this, several methods used to evaluate the total iron concentration in *p*-Si rely on breaking the FeB pair [6, 7, 8]. Second, the recombination activity of these centers must be considered, as it depends on the defect energy level relative to the Fermi level and the charge carrier capture cross-section. Interstitial iron and FeB pairs are among the most detrimental recombination-active impurities in *p*-Si [1, 9] in contrast to other iron-related defects. Notably, iron gettering by oxygen precipitates or structural defects increases carrier lifetime [10, 11]. In *n*-Si, Fe_i is not a recombination-active impurity due to the filling of its energy level. Reducing the impact of iron through gettering during phosphorus diffusion [10, 11, 12] or the formation of a passivating layer [13] is well-established and used in the solar cell industry.

Thus, our assumption that the primary influence of iron impurities in the *p*-regions of a solar cell on photoelectric parameters is due to Fe_iB_{Si} pairs and Fe_i is fully justified. Furthermore, we emphasize that this paper focuses on the relative changes in parameters during Fe_iB_{Si} \rightleftharpoons Fe_i + B_{Si} transformation, which enables the isolation of these specific defects’ contributions.

This answer is incorporated in the revised text on page 5, two last paragraph in Section 2.1. Simulation Details.

Comment 2. *The author should give the transient nature of defect dynamics, how do you assess the long-term stability of silicon solar cells in the presence of iron contamination? What experimental approaches would you recommend to study the aging effects of these defects over time?*

Reply:

Interstitial iron atoms exhibit high mobility in silicon [1]. For example, the characteristic time required for FeB pair formation, which depends on the diffusion coefficient of Fe_i, is given by the following expression [14, 15, 16]:

$$\tau = 5.7 \times 10^5 \frac{\text{s}}{\text{K cm}^3} \times \frac{T}{p} \exp\left(\frac{0.65}{kT}\right). \quad (1)$$

where *p* is the doping level.

That is, at room temperature, the formation of an equilibrium concentration of FeB pairs is completed within 24 hours, while at *T* = 340 K, the τ is approximately 10 minutes. Therefore, iron contamination is not a determining factor in the long-term stability of silicon solar cells, unlike sodium atoms, which are considered one of the primary contributors to potential-induced degradation [17].

The information on the characteristic time of FeB pair formation has been added to the revised manuscript (page 5, last paragraph in Section 2.2.).

The measurements were carried over the temperature range of 300-340 K. The sample temperature was driven by a thermoelectric cooler controlled by an STS-21 sensor and maintained constant by a PID algorithm embedded in the software that serves the experimental setup. **Notably, the characteristic time for FeB pair recovery after the cessation of illumination is approximately 13,000 seconds at 300 K and only 600 seconds at 340 K [14, 15]. These limitations affect the measurement duration at high temperatures, and the experiments accounted for them.**

Comment 3. *An Author should provide a theoretical framework for understanding how the temperature range you studied (290 K to 340 K) influences the activation energy of iron-related defects? How might this affect the performance of solar cells in varying environmental conditions?*

Reply:

The temperature range studied in our work (290 K to 340 K) was chosen to reflect realistic operating conditions of silicon solar cells, particularly those exposed to moderate climate variations. The behavior of iron-boron (Fe_iB_s) pairs and interstitial iron (Fe_i) is strongly temperature-dependent due to thermal excitation and defect migration effects. The key theoretical considerations include:

- Thermal dissociation of Fe_iB_s pairs:

- the equilibrium between Fe_iB_s pairs and free Fe_i follows an Arrhenius-type relation, governed by the dissociation rate:

$$k_d = k_0 \exp\left(-\frac{E_a}{k_b T}\right), \quad (2)$$

where k_d is the dissociation rate, E_a is the activation energy of Fe_iB_s dissociation, k_b is the Boltzmann constant, and T is the absolute temperature;

- prior studies estimate $E_a \approx 0.7 - 0.8$ eV for Fe_iB_s dissociation in silicon;
- as temperature increases, Fe_iB_s pairs dissociate more readily, increasing Fe_i concentration, which enhances recombination activity and reduces carrier lifetimes.

- Shockley-Read-Hall recombination dependence:

- the capture cross-section (σ) of Fe_i defects is temperature-dependent, influencing the recombination rate U given by:

$$U = \frac{\sigma v_{th} N_d}{1 + \exp\left(\frac{E_t - E_F}{k_b T}\right)}, \quad (3)$$

where v_{th} is the thermal velocity of carriers, N_d is defect concentration, and E_t is the defect energy level;

- as temperature rises, carrier thermal velocity increases, altering the recombination dynamics and further impacting photovoltaic parameters.

The temperature-dependent behavior of iron-related defects has direct consequences on solar cell operation under different environmental conditions:

- Reduction in open-circuit voltage (V_{OC}):

- increased FeB dissociation at high temperatures raises Fe_i concentration, enhancing Shockley-Read-Hall recombination. Since V_{OC} is governed by the equation:

$$V_{OC} = \frac{k_b T}{q} \log\left(\frac{I_{SC}}{I_0} + 1\right), \quad (4)$$

where I_0 is the saturation current, higher recombination rates increase I_0 , leading to a reduction in V_{OC} ;

- the observed temperature coefficient of ($V_{OC} \approx -2.3 \frac{mV}{K}$) aligns with known iron-related degradation effects.
- Short-circuit current I_{SC} variability:
 - as Fe_i concentration rises, the minority carrier lifetime decreases, reducing carrier collection efficiency and thus I_{SC} . However, in certain temperature ranges, increased carrier mobility may partially compensate for these losses.
- Thermal cycling and long-term degradation risks:
 - field-deployed solar cells experience daily temperature fluctuations, which can lead to repeated FeB dissociation and recombination cycles, contributing to metastable defect states. Over time, Fe_i precipitation may lead to irreversible efficiency losses, especially in high-temperature climates.

Comment 4. *An Author mentioned the application of principal component analysis in evaluating impurity levels. Could you elaborate on how this technique was implemented in your study and its effectiveness in distinguishing between different types of impurities?*

Reply:

Comment 5. *Your paper discusses the influence of doping levels on the response of solar cells to iron contamination. Author should explain how varying the doping concentration affects the sensitivity of photovoltaic parameters to iron presence through the reference: Augmented photovoltaic performance of Cu/Ce-(Sn: Cd)/n-Si Schottky barrier diode utilizing dual-doped Ce-(Sn: Cd) thin films.*

Reply:

The primary reason doping concentration N_B influences the sensitivity of photovoltaic parameters to iron presence is that the N_B determines the Fermi level E_F position. In turn, the rate of Shockley-Read-Hall recombination — and consequently, variations in photovoltaic parameters due to iron impurities — depends on the relative positioning of E_F concerning the Fe_iB_s and Fe_i levels. Additionally, the equilibrium ratio of Fe_iB_s and Fe_i concentrations is also determined by the Fermi level position [18, 19]. Therefore, N_B affects the number of defects that change their state due to the complete dissociation of Fe_iB_s pairs, leading to corresponding relative changes in photovoltaic parameters analyzed in this study. Besides, the N_B concentration also affects the SCR depth (see Fig. 4 in manuscript). The ratio of different charge states for both interstitial iron atoms and iron-boron pairs differs between the SCR and the bulk of the base, leading to distinct SRH recombination rates and variations in photovoltaic conversion efficiency for structures with different doping levels. Furthermore, according to Klaassen's model [20], the concentration of ionized impurities influences charge carrier mobility and, consequently, the diffusion coefficient D_n , diffusion length L_n , and photoelectric conversion efficiency (see Eqs. (4), (5), and (7) in the manuscript). However, the effect of N_B via D_n and L_n is significantly weaker than its influence through E_F and SCR depth variations. Minor effects are expected as well due to both bandgap narrowing and changes in light absorption by free carriers with varying doping levels. The impact of doping level on photovoltaic parameters has been studied in heterojunction [21], thin-film [22], and perovskite [23] solar cells. Moreover, it has been shown [22] that doping concentration variations affect other barrier structure parameters, such as saturation current and ideality factor.

This answer is incorporated in the text on page 4, paragraph 4, line 1-2. Reference is included in the revised manuscript (references 1)

...while the presence of the acceptor state Fe_iB_s causes the carrier lifetime to be doping-dependent under low injection conditions [FeB:Schmidt].

The relationship between N_B and E_F is the key factor in the influence of doping level on the sensitivity of photovoltaic parameters to iron presence. Specifically, the rate of SRH recombination — and consequently, variations in photovoltaic parameters due to iron impurities — depends on the relative positioning of E_F concerning the Fe_iB_s and Fe_i levels. Additionally, the equilibrium ratio of Fe_iB_s and Fe_i concentrations is

also determined by the Fermi level position [FeB:kinetic,MurphyJAP2011]. Therefore, N_B affects the number of defects that change their state due to the complete dissociation of Fe_iB_s pairs, leading to corresponding relative changes in photovoltaic parameters analyzed in this study. Besides, the N_B concentration also affects the SCR depth (see Fig. 4). The ratio of different charge states for both interstitial iron atoms and iron-boron pairs differs between the SCR and the bulk of the base, leading to distinct SRH recombination rates and variations in photovoltaic conversion efficiency for structures with different doping levels. Furthermore, according to Klaassen's model [KLAASSEN953], the concentration of ionized impurities influences charge carrier mobility and, consequently, the diffusion coefficient D_n , diffusion length L_n , and photoelectric conversion efficiency (see Eq. (4)). However, the effect of N_B via D_n and L_n is significantly weaker than its influence through E_F and SCR depth variations. Minor effects are expected as well due to both bandgap narrowing and changes in light absorption by free carriers with varying doping levels. The impact of doping level on photovoltaic parameters has been studied in heterojunction [8], thin-film [10], and perovskite [6] solar cells. Moreover, it has been shown [10] that doping concentration variations affect other barrier structure parameters, such as saturation current and ideality factor.

Comment 6. *In your findings, Author mentions that changes in short-circuit current under monochromatic illumination are the most reliable for estimating iron concentration. An author should provide more details on the methodology used to derive this conclusion and any potential limitations of this approach?*

Reply:

Comment 7. *An Author must improve the introduction section in the application part through the recent references CuO-La2O3 Composite-Enabled MIS Schottky Barrier Diodes: A Novel Approach to Optoelectronic Device Diversification; Enhancing photovoltaic applications through precipitating agents in ITO/CIS/CeO2/Al heterojunction solar cell; Manifestation on the choice of a suitable combination of MIS for proficient Schottky diodes for optoelectronics applications: A comprehensive review.*

[24, 25, 26]

We sincerely thank the Reviewer for suggesting the inclusion of recent references (cited as References 2, 3, and 9 in the revised manuscript). Below, we present an improved version of the 1st paragraph of Introduction.

The necessity for renewable energy sources to meet the growing global demand for sustainable and environmentally friendly energy alternatives has become evident. Among the wide range of renewable energy sources, sunlight is the cleanest, safest, and most abundant source for use in sustainable energy to support economic growth [1]. The utilization of solar energy heavily depends on the use of photovoltaic cells. The development of next-generation solar cells is primarily driven by the search for novel materials suitable for their fabrication. Particular attention is given to exploring the potential use of composites and nanoparticles (e.g., Cu-La-based systems [2], cerium oxide, and copper indium sulfate [3]), MAX phases [4,5], and chalcogenides (such as GeSe, MoSe₂, Sb₂Se₃, and SnSe as hole transport materials [6] or SnS₂ and WS₂ as electron transport materials [7]), as well as metal silicides (e.g., FeSi₂ as an absorber layer [8]). These studies cover a broad range of materials [9], with the primary goal of developing highly efficient and cost-effective photovoltaic devices. Frequently, these novel materials are integrated with silicon in solar cells [8,10]. However, it is worth noting that traditional silicon-based devices continue to play a dominant role in the photovoltaic market [11,12].

Reply:

Response to Reviewer #2

Comment 1. *The abstract section should be more informative.*

Reply:

Comment 2. *The novelty of the work is missing in the introduction. Authors should explain what are the key advantages of iron's impact on silicon solar cell?*

Reply:

Comment 3. Authors should improve the image quality of all figures.

Reply:

Comment 4. Author should explain how does the band alignment affect the overall performance of the solar cell?

Reply:

Comment 5. What are the primary sources of iron contamination in silicon used for solar cells?

Reply:

Comment 6. What role do recombination centers created by iron play in the modeling of solar cell performance?

Reply:

Comment 7. Author should discuss and cited recent Si based solar cell in the revised manuscript: DOI : 10.1016/j.mseb.2024.117360, DOI : 10.1016/j.mseb.2023.117141, DOI : 10.1016/j.mseb.2024.117817, DOI : 10.1007/s42247-024-00821-y, DOI : 10.1016/j.inoche.2024.112785

Reply:

We sincerely appreciate the reviewer's valuable suggestion. Most of the recommended works are highly relevant, and we have cited them in multiple sections of the manuscript. Advised articles are referenced as References 8, 4, 6, 7, and 5 in the revised version.

So, we discuss and cited suggested papers in the Introduction, first paragraph

The necessity for renewable energy sources to meet the growing global demand for sustainable and environmentally friendly energy alternatives has become evident. Among the wide range of renewable energy sources, sunlight is the cleanest, safest, and most abundant source for use in sustainable energy to support economic growth [1]. The utilization of solar energy heavily depends on the use of photovoltaic cells. **The development of next-generation solar cells is primarily driven by the search for novel materials suitable for their fabrication. Particular attention is given to exploring the potential use of composites and nanoparticles (e.g., Cu-La-based systems [2], cerium oxide, and copper indium sulfate [3]), MAX phases [4,5], and chalcogenides (such as GeSe, MoSe₂, Sb₂Se₃, and SnSe as hole transport materials [6] or SnS₂ and WS₂ as electron transport materials [7]), as well as metal silicides (e.g., FeSi₂ as an absorber layer [8])**

on page 3, first paragraph from the top

Despite its one-dimensional modeling approach, SCAPS is extensively used for modeling various types of solar cells [6,7,8,Joshi2024,Ravidas2024,Liu2024,You2023] in general and for investigating the effects of defects on their performance [6,8,AitAbdelkadir2023,Liang2024,SCAPSDefect3] in particular.

on page 4, last paragraph

Impact of change of iron defects was investigated as a function of temperature from 290 K to 340 K, base depth from 180 μm to 380 μm , base doping level from 10^{15} cm^{-3} to 10^{17} cm^{-3} , and total impurity iron atom concentration from 10^{10} cm^{-3} to 10^{14} cm^{-3} . **It is worth noting that investigating the effects of doping density, defect density, temperature, and active layer thickness on photovoltaic parameters is a well-established practice [6,7,8].** For each illumination scenario, calculations were carried out with 11 different temperature values and 5 base depth values, evenly distributed within the specified ranges.

on page 7, 3rd paragraph from the bottom

However, the effect of N_B via D_n and L_n is significantly weaker than its influence through E_F and SCR depth variations. Minor effects are expected as well due to both bandgap narrowing and changes in light absorption by free carriers with varying doping levels. **The impact of doping level on photovoltaic parameters has been studied in heterojunction [8], thin-film [10], and perovskite [6] solar cells.** Moreover, it has been shown [10] that doping concentration variations affect other barrier structure parameters, such as saturation current and ideality factor.

on page 7, 4th paragraph from the top

- At low boron concentrations ($N_B < 10^{16} \text{ cm}^{-3}$), the dependence of ϵFF on N_{Fe} is notably non-linear. Within the used concentration range, two regions of decrease and two regions of increase in ϵFF are observed. **A similar**

relationship between the fill factor and defect concentration was observed in BaZrSe₃-based perovskite solar cells [6];

Comment 8. *How does the modeling in this study contribute to the design of processes for impurity control in silicon?*

Reply:

Comment 9. *State the main findings in the conclusions.*

Reply:

References

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